GP2814

Application No. 09/440,928 Attorney Docket 040301-0578

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD OF MANUFACTURING THE SAME

Appl. No.: 09/440,928

Filing Date: 11/16/1999

Examiner: S. Rao

Art Unit: 2814

AMENDMENT TRANSMITTAL

Mail Stop Fee Amendment
Commissioner for Patents
PO Box 1450
Alexandria, Virginia 22313-1450

Sir:

Transmitted herewith is an Amendment and Reply in the above-identified application.

[ ] Small Entity status under 37 C.F.R. § 1.9 and § 1.27 has been established by a Small Entity statement previously submitted.

[ ] Small Entity statement is enclosed.

[**X**] The fee required for additional claims is calculated below:

	Claims as Amended		Previously Paid For		Extra Claims Present		Rate		Additional Claims Fee
Total Claims:	30	–	28	=	2	x	$18.00	=	$36.00
Independents:	10	–	8	=	2	x	$84.00	=	$168.00
First presentation of any Multiple Dependent Claims:						+	$280.00	=	$0.00
							CLAIMS FEE TOTAL:	=	$204.00

[ ] Applicant hereby petitions for an extension of time under 37 C.F.R. §1.136(a) for the total number of months checked below:

[ ]	Extension for response filed within the first month:	$110.00	$0.00
[ ]	Extension for response filed within the second month:	$410.00	$0.00
[ ]	Extension for response filed within the third month:	$930.00	$0.00
[ ]	Extension for response filed within the fourth month:	$1,450.00	$0.00
[ ]	Extension for response filed within the fifth month:	$1,970.00	$0.00
	EXTENSION FEE TOTAL:		$0.00
[ ]	Statutory Disclaimer Fee under 37 C.F.R. 1.20(d):	$110.00	$0.00
	CLAIMS, EXTENSION AND DISCLAIMER FEE TOTAL:		$204.00
[ ]	Small Entity Fees Apply (subtract ½ of above):		$0.00
	TOTAL FEE:		$204.00

[ ] Please charge Deposit Account No. 19-0741 in the amount of $204.00. A duplicate copy of this transmittal is enclosed.

[X] A check in the amount of $204.00 for additional claims fee is enclosed.

[X] The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741. If any extensions of time are needed for timely acceptance of papers submitted herewith, applicant hereby petitions for such extension under 37 C.F.R. §1.136 and authorizes payment of any such extensions fees to Deposit Account No. 19-0741.

Please direct all correspondence to the undersigned attorney or agent at the address indicated below.

Respectfully submitted,

Date May 27, 2003
(Tuesday after holiday)

By Aaron C. Chatterjee

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Attorney Docket 040301-0578

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J. Artis

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nobutoshi AOKI et al.

Title: SEMICONDUCTOR INTEGRATED CIRCUIT INCLUDING INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD OF MANUFACTURING THE SAME

Appl. No.: 09/440,928

Filing Date: November 16, 1999

Examiner: S. Rao

Art Unit: 2814

AMENDMENT AND REPLY UNDER 37 C.F.R. § 1.111

Mail Stop FEE AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

In reply to the Office Action mailed February 25, 2003, please amend the above-identified application as follows:

IN THE DRAWINGS:

FIG. 3 has been amended as shown in red on the drawings attached to the Proposed Changes to the Drawings, being filed concurrently herewith.

IN THE CLAIMS:

Please amend the claims by replacing the indicated claims with the following clean version. (See **Attachment A** for the marked up version of the amended claims.)

1. (Five Times Amended) A semiconductor device comprising:

F1 a pair of main electrodes used as source and drain electrodes;

a channel forming region provided between the pair of main electrodes;

an insulating gate film formed on the channel forming region; and